

2SD1581

NPN SILICON TRANSISTOR

NPN SITICON EPITAXIAL TRANSISTOR FOR LOW-FREQUENCY POWER AMPLIFIERS

DESCRIPTION

The UTC **2SD1581** is a single type super high hFE transistor and low collector saturation voltage and low power loss. This transistor is ideal for use in high current drives such as mortars, relays, and ramps.

FEATURES

- * Ultra high h_{FE}
- h_{FE} = 800 to 3200 (@ V_{CE}=5.0V, I_C=500mA)
- * Low collector saturation voltage
- $V_{CE(SAT)}$ =0.18V Typ. (@I_C=1.0A, I_B=10mA)

ORDERING INFORMATION

Ordering Number		Deekege	Pin Assignment			Decking
Lead Free	Halogen Free	гаскауе	1	2	3	Packing
2SD1581L-x-T60-K	2SD1581G-x-T60-K	TO-126	Е	С	В	Bulk
Note: Pin Assignment: E: Em	itter C: Collector B: Bas	se				

(1) K: Bulk
(2) T60: TO-126
(3) x: refer to Classification of h _{FE1}
(4) G: Halogen Free and Lead Free, L: Lead Free
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MARKING





■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		B _{VCBO}	30	V
Collector-emitter voltage		B _{VCEO}	25	V
Emitter-Base Voltage		B _{VEBO}	15	V
Collector Current	DC		2	A
Collector Current	Pulse	IC	3 (Note 2)	A
Collector Dissipation		Pc	1	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-50 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse Test : Pulse width \leq 10ms, Duty cycle \leq 50%.

■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cutoff Current	I _{CBO}	V _{CB} =30V, I _E =0A			100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =10V, I _C =0A			100	nA
DC Current Cain	h_{FE1}	V _{CE} =5V, I _C =500mA	800	1500	3200	
	h _{FE2}	V _{CE} =5V, I _C =2A	400			
Collector Saturation Voltage	$V_{CE(SAT)}$	I _C =1A, I _B =10mA		0.18	0.3	V
Base Saturation Voltage	$V_{BE(SAT)}$	I _C =1A, I _B =10mA		0.83	1.2	V
Output Capacitance	C _{OB}	V _{CB} =10V, I _E =0A, f=1MHz		26	35	pF
Current Gain Bandwidth Product	f⊤	V _{CE} =10V, I _E =-500mA	150	350		MHz

CLASSIFICATION OF h_{FE1}

RANK	М	L	К
RANGE	800 ~ 1600	1200 ~ 2400	2000 ~ 3200



TYPICAL CHARACTERISTICS











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